ELC 4383 – RF/Microwave Circuits I Mixers/Diodes Supplemental Homework

SMD.1. A mixer is designed to receive an RF input signal at a frequency of 3000 MHz and downconvert it to an IF signal at 400 MHz. Assume that the following power levels are measured at the ports of a frequency-conversion system containing the mixer and necessary filtering:



(a) If the local oscillator frequency is higher than the RF frequency, give the LO frequency and the image frequency.

(b) Calculate the conversion loss.

(c) Calculate the RF-to-IF isolation.

SMD.2. A mixer is designed to receive an RF input signal at a frequency of 4000 MHz and downconvert it to an IF signal at 200 MHz. Assume that the following power levels are measured at the ports of a frequency-conversion system containing the mixer and necessary filtering:



(a) If the local oscillator frequency is higher than the RF frequency, give the LO frequency and the image frequency.

(b) Calculate the conversion loss.

(c) Calculate the RF-to-IF isolation.

SMD.3. A mixer is designed to receive an RF input signal at a frequency of 8000 MHz and downconvert it to an IF signal at 700 MHz. Assume that the following power levels are measured at the ports of a frequency-conversion system containing the mixer and necessary filtering:



(a) If the local oscillator frequency is higher than the RF frequency, give the LO frequency and the image frequency.

- (b) Calculate the conversion loss.
- (c) Calculate the LO-to-IF isolation.

SMD.4. A mixer contains a diode with the following parameters: $C_j = 0.7 \text{ pF}$, $R_s = 5 \Omega$, $I_s = 20 \mu \text{A}$, and $L_p = C_p = 0$. Use $\alpha = 1/(25 \text{ mV})$. Compute the open-circuit voltage sensitivity at 5 GHz for $I_0 = 100 \mu \text{A}$.

SMD.5. A mixer contains a diode with the following parameters: $C_j = 0.9 \text{ pF}$, $R_s = 2 \Omega$, $I_s = 15 \mu \text{A}$, and $L_p = C_p = 0$. Use $\alpha = 1/(25 \text{ mV})$. Compute the open-circuit voltage sensitivity at 1.5 GHz for $I_0 = 20 \text{ mA}$.